# 2N5151U3 &2N5153U3

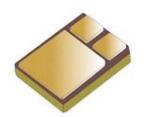


## **PNP Power Silicon Transistor**

Rev. V3

#### **Features**

- JANS and JANSR Qualified to MIL-PRF-19500/545
- JEDEC Registered 2N5153
- Lightweight & Low Power
- Ideal for Space, Military, and Other High Reliability Applications
- Surface Mount U3 Package



## **Electrical Characteristics**

| Parameter   | Test Conditions  | Symbol                      | Units        | Min.     | Max.           |
|---|--|-----------------------------|--------------|----------|----------------|
| Off Characteristics   |  |                             |              |          |                |
| Collector - Emitter Breakdown Voltage   | I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = 0   | V <sub>(BR)CEO</sub>        | Vdc          | -80      | _              |
| Emitter - Base Cutoff Current   | $V_{EB} = -4.0 \text{ Vdc}, I_{C} = 0$<br>$V_{EB} = -5.5 \text{ Vdc}, I_{C} = 0$                       | I <sub>EBO</sub>            | µAdc<br>mAdc | _        | -1<br>-1       |
| Collector - Emitter Cutoff Current  | $V_{CE} = -60 \text{ Vdc}, V_{BE} = 0$<br>$V_{CE} = -100 \text{ Vdc}, V_{BE} = 0$                      | I <sub>CES</sub>            | µAdc<br>mAdc | _        | -1<br>-1       |
| Collector - Emitter Cutoff Current  | $V_{CE} = -40 \text{ Vdc}, I_B = 0$  | I <sub>CEO</sub>            | μAdc         | _        | -50            |
| On Characteristics <sup>1</sup>   |  |                             |              |          |                |
| Forward Current Transfer Ratio  | $I_C$ = -50 mAdc, $V_{CE}$ = -5.0 Vdc<br>2N5151U3<br>2N5153U3<br>$I_C$ = -2.5 Adc, $V_{CE}$ = -5.0 Vdc |                             |              | 20<br>50 | _              |
|   | 2N5151U3<br>2N5153U3   | H <sub>FE</sub>             | -            | 30<br>70 | 90<br>200      |
|   | $I_C$ = -5.0 Adc, $V_{CE}$ = -5.0 Vdc<br>2N5151U3<br>2N5153U3  |                             |              | 20<br>40 | _<br>_         |
| Collector - Emitter Saturation Voltage  | $I_C$ = -2.5 Adc, $I_B$ = -250 mAdc<br>$I_C$ = -5.0 Adc, $I_B$ = -500 mAdc                             | V <sub>CE(SAT)</sub>        | Vdc          | _        | -0.75<br>-1.50 |
| Emitter - Base Voltage Non-Saturation   | $I_C = -2.5 \text{ Adc}, V_{CE} = -5.0 \text{ Vdc}$  | V <sub>BE(ON)</sub>         | Vdc          | _        | -1.45          |
| Emitter - Base Saturation Voltage   | $I_C$ = -2.5 Adc, $I_B$ = -250 mAdc<br>$I_C$ = -5.0 Adc, $I_B$ = -500 mAdc                             | $V_{\text{BE}(\text{SAT})}$ | Vdc          | _        | -1.45<br>-2.20 |
| Dynamic Characteristics   |  |                             |              |          |                |
| Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio | $I_{C}$ = -500 mAdc, $V_{CE}$ = -5.0 Vdc, f = 10 mHz 2N5151U3 2N5153U3                                 | H <sub>FE</sub>             | -            | 6<br>7   | _              |
| Small-Signal Short-Circuit Forward Current<br>Transfer Ratio                          | $I_C$ = -100 mAdc, $V_{CE}$ = -5.0 Vdc, f = 1 kHz 2N5151U3 2N5153U3                                    | H <sub>FE</sub>             | -            | 20<br>50 | _              |
| Output Capacitance  | V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1 MHz   | C <sub>OBO</sub>            | pF           | _        | 250            |
|   |  | l                           |              |          | L              |

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<sup>1.</sup> Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤2.0%.

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## **Electrical Characteristics**

| Parameter                 | Test Conditions   | Symbol           | Units | Min. | Max. |  |  |  |
|---------------------------|---|------------------|-------|------|------|--|--|--|
| Switching Characteristics |   |                  |       |      |      |  |  |  |
| Turn-On Time              |   | T <sub>ON</sub>  | μs    | _    | 0.5  |  |  |  |
| Turn-Off Time             | $I_C = -5 \text{ Adc}; I_{B1} = -500 \text{ mAdc}, R_L = 6 \Omega,$ | T <sub>OFF</sub> | μs    | _    | 1.5  |  |  |  |
| Storage Time              | $I_{B2} = -500 \text{ mAdc}, V_{BE(OFF)} = -3.7 \text{ Vdc}$        | Ts               | μs    | _    | 1.4  |  |  |  |
| Fall Time                 |   | T <sub>f</sub>   | μs    | _    | 0.5  |  |  |  |

#### Safe Operating Area

 $\begin{array}{lll} \text{DC Tests:} & T_{\text{C}} = +25^{\circ}\text{C}, \text{ I Cycle}, \text{ t} = 1 \text{ s} \\ \text{Test 1:} & V_{\text{CE}} = -5 \text{ Vdc}, \text{ I}_{\text{C}} = -2 \text{ Adc} \\ \text{Test 2:} & V_{\text{CE}} = -32 \text{ Vdc}, \text{ I}_{\text{C}} = -310 \text{ mAdc} \\ \text{Test 3:} & V_{\text{CE}} = -80 \text{ Vdc}, \text{ I}_{\text{C}} = -12.5 \text{ mAdc} \\ \end{array}$ 

## **Absolute Maximum Ratings<sup>2,3</sup>**

| Ratings  | Symbol           | Value              |
|--|------------------|--------------------|
| Collector - Emitter Voltage  | $V_{CEO}$        | -80 Vdc            |
| Collector - Base Voltage   | V <sub>CBO</sub> | -100 Vdc           |
| Emitter - Base Voltage   | V <sub>EBO</sub> | -5.5 Vdc           |
| Collector Current  | I <sub>C</sub>   | -2 Adc<br>-10 Adc⁴ |
| Total Power Dissipation  @ $T_A = 25^{\circ}C$ @ $T_C = 25^{\circ}C$ | P <sub>T</sub>   | 1.16 W<br>100 W    |
| Operating & Storage Temperature Range                                | $T_J, T_{STG}$   | -65°C to +200°C    |

- 2. Derate linearly 5.7 mW/°C for  $T_A > +25$ °C.
- 3. Derate linearly 571 mW/°C for  $T_A > +25$ °C.
- 4. This value applies for PW ≤ 8.3 ms, duty cycle ≤ 1%.

## **Thermal Characteristics**

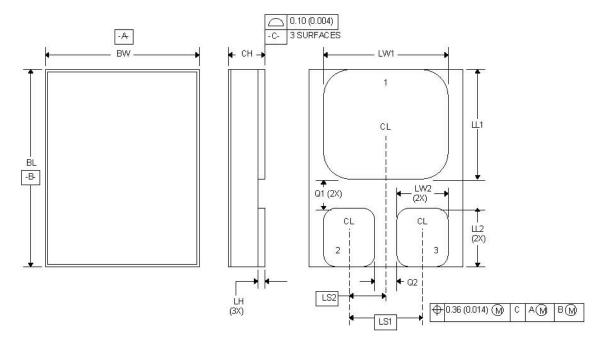
| Characteristics                      | Symbol          | Max. Value |
|--------------------------------------|-----------------|------------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.75°C/W   |



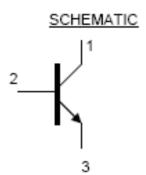
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## **Outline Drawing (U3)**



- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
- 4. Terminal 1 collector, terminal 2 -base, terminal 3 emitter.



|                 | Dimensions |        |          |       |  |
|-----------------|------------|--------|----------|-------|--|
| Ltr             | Inches     |        | Millim   | eters |  |
|                 | Min.       | Max.   | Min.     | Max.  |  |
| BL              | 0.395      | 0.405  | 10.03    | 10.29 |  |
| BW              | 0.291      | 0.301  | 7.40     | 7.65  |  |
| CH              | 0.1085     | 0.1205 | 2.76     | 3.06  |  |
| LH              | 0.010      | 0.020  | 0.25     | 0.51  |  |
| LW <sub>1</sub> | 0.281      | 0.291  | 7.14     | 7.39  |  |
| LW <sub>2</sub> | 0.090      | 0.100  | 2.29     | 2.54  |  |
| LL <sub>1</sub> | 0.220      | 0.230  | 5.59     | 5.84  |  |
| LL <sub>2</sub> | 0.115      | 0.125  | 2.92     | 3.18  |  |
| LS <sub>1</sub> | 0.150 BSC  |        | 3.81 BSC |       |  |
| LS <sub>2</sub> | 0.075 BSC  |        | 1.91 BSC |       |  |
| Q <sub>1</sub>  | 0.030      |        | 0.762    |       |  |
| $Q_2$           | 0.030      |        | 0.762    |       |  |

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